

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

For a detailed explanation of implementing these values in P-Spice, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-Spice Platform](#).

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	11.1229	N/A	1.1121
RT2	18.8666	N/A	4.7779
RT3	45.8097	N/A	1.1097
RT4	9.2008	N/A	13.0003
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.2796 m	N/A	655.6456 u
CT2	3.9286 m	N/A	5.8821 m
CT3	1.3734	N/A	262.0076 m
CT4	182.5361 m	N/A	2.0022 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	14.3727	N/A	4.0537
RF2	15.8853	N/A	14.8545
RF3	10.7666	N/A	787.3600 m
RF4	43.9754	N/A	304.4400 m
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	871.6762 u	N/A	656.2894 u
CF2	2.5486 m	N/A	1.0594 m
CF3	135.4187 m	N/A	246.2120 m
CF4	1.2704	N/A	2.3664 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

